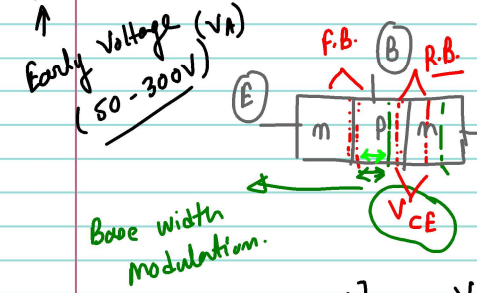
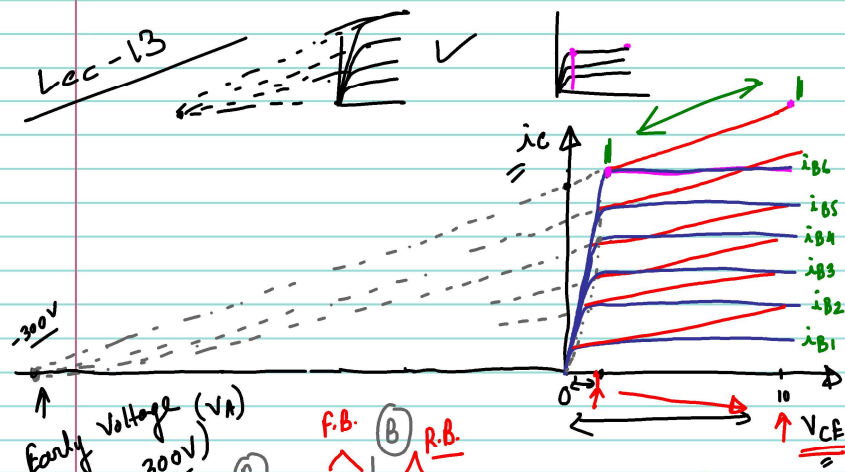
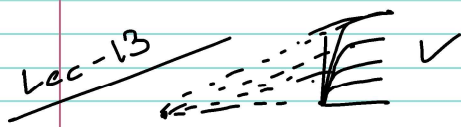
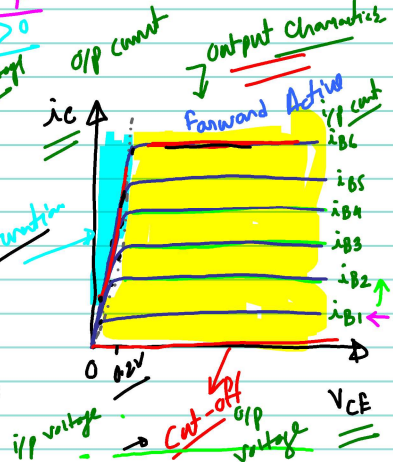
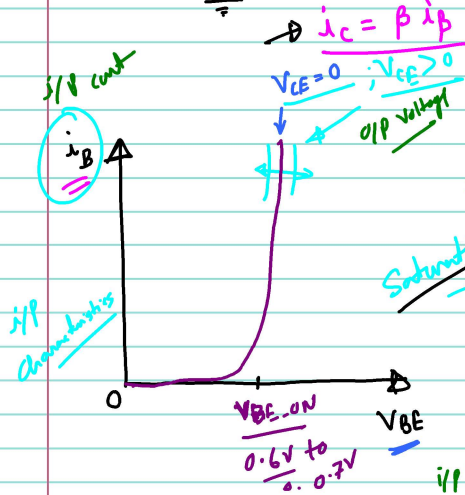
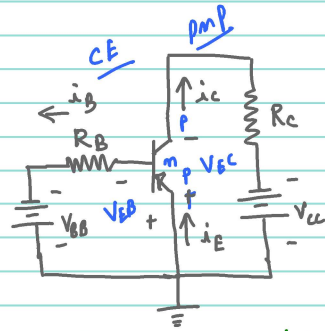
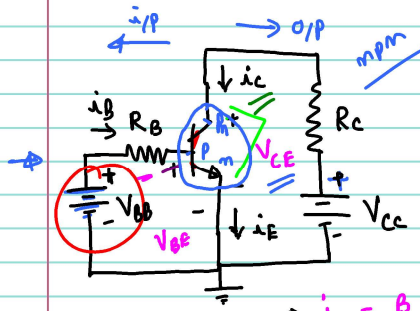
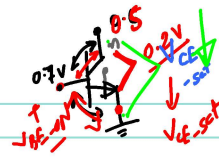


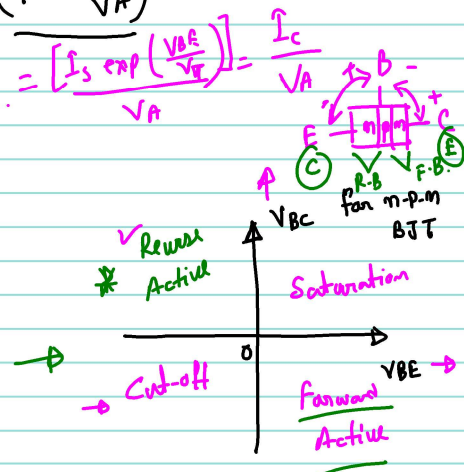
Common Emitter circuit (CE):



Active region $i_C = I_S \exp\left(\frac{V_{BE}}{V_T}\right) \left(1 + \frac{V_{CE}}{V_A}\right)$

$\frac{1}{r_o} = \frac{\partial i_C}{\partial V_{CE}} \bigg|_{V_{BE} = \text{const.}} = \frac{I_C}{V_A}$

$r_o = \frac{V_A}{I_C}$



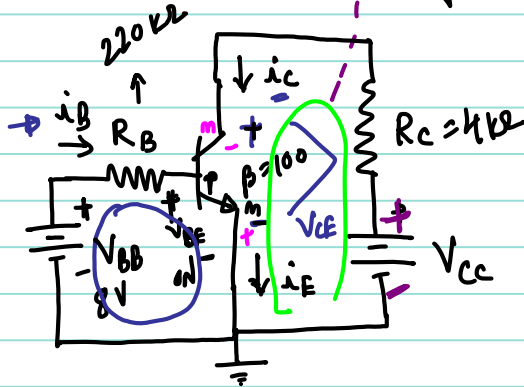
So, BJT is in Saturation [$i_c \neq \beta i_b$]

$V_{CE-sat} = 0.2V$, KVL in outer loop,

$$i_c = \frac{V_{CC} - V_{CE(sat)}}{R_C} = \frac{10 - 0.2}{4} = 2.45 \text{ mA}$$

$$C.E. \text{ curt gain} = \frac{i_c}{i_b} = \frac{2.45 \text{ mA}}{33.2 \mu A} \approx 74$$

BJT Circuit : DC Analysis



Given that,

$$V_{CC} = 10V, R_C = 4k\Omega$$

$$V_{BB} = 8V, R_B = 220k\Omega$$

$$\beta = 100$$

$$i_B = \frac{8 - 0.7}{220k\Omega} = 33.2 \mu A$$

Assuming, BJT is in Forward Active Mode

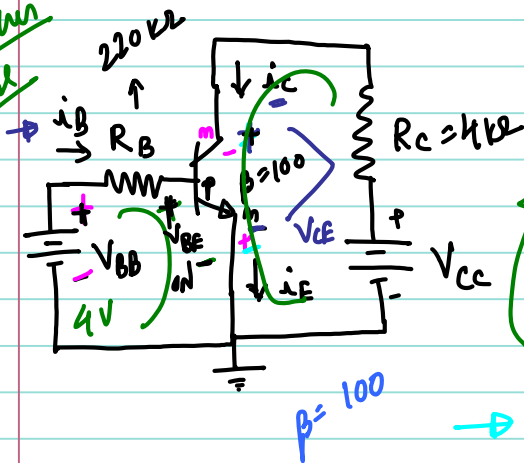
$$i_C = \beta i_B = 100 \times 33.2 \mu A$$

$$i_C = 3.32 \text{ mA}$$

$$V_{CE} = V_{CC} - I_C R_C = 10 - 3.32 \times 4 = -3.28V$$

Assumption was not correct.

Another case



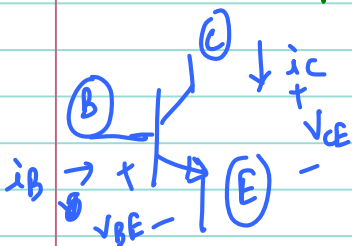
only, V_{BB} is changed to 4V.

$$i_B = \frac{4 - 0.7}{220k\Omega} = 15 \mu A$$

Assume, Active mode of operation
 $i_C = \beta i_B = 1.5 \text{ mA}$

$$V_{CE} = V_{CC} - i_C R_C = 4V$$

Calculate the power dissipation in the BJT



$$P_T = i_B \cdot V_{BE} + i_C \cdot V_{CE}$$

$$P_T = i_C \cdot V_{CE} = 1.5 \text{ mA} \times 4V$$

$$P_T = 6 \text{ mW}$$

BJT DC Analysis: (n-p-n)

(i) Assume BJT is in forward active mode

→ $V_{BE} = V_{BE(on)} \approx 0.7V$ for Silicon BJT

$I_B > 0$ and $I_C = \beta I_B$ ←

(ii) Analyze the 'linear' circuit.

(iii) If $V_{CE} > V_{CE(sat)} \rightarrow$ then active region (our assumption is correct)

→ if $V_{CE} < 0 \rightarrow$ Probably, BJT is in saturation

→ if $I_B < 0 \rightarrow$ Probably BJT is in cut-off

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Load line:

